

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (currently amended) A method for making micromechanical structures having at least one lateral gap therebetween, the method comprising:

providing a substrate;

surface micromachining the substrate to form a ~~first~~ capacitively-driven, lateral micromechanical structure having a first vertical sidewall and a sacrificial spacer layer on the first vertical sidewall;

~~forming a second micromechanical structure~~ a first capacitive transducer electrode on the substrate, the ~~second micromechanical structure~~ first capacitive transducer electrode including a second vertical sidewall separated from the first vertical sidewall by the spacer layer; and

removing the spacer layer to form a first lateral submicron capacitive gap between the ~~first and second micromechanical structures~~ structure and the first capacitive transducer electrode to increase electromechanical coupling therebetween.

2. (currently amended) The method as claimed in claim 1 wherein the step of surface micromachining further forms a third vertical sidewall on the ~~first~~ micromechanical structure with the sacrificial spacer layer thereon and wherein the method further comprises forming a ~~third micromechanical structure~~ second capacitive transducer electrode including a fourth vertical sidewall separated from the third vertical sidewall by the spacer layer and wherein the step of removing further forms a second lateral submicron gap between the ~~first and third micromechanical structures~~ structure and the second capacitive transducer electrode.

3. (cancel)

4. (currently amended) The method as claimed in claim 3 1 wherein the ~~first~~ micromechanical structure includes a resonator and wherein the first lateral submicron capacitive gap is an electrode-to-resonator capacitive gap.

5. (currently amended) The method as claimed in claim 1 wherein the step of forming includes the step of plating metal on the substrate and wherein the first capacitive transducer electrode ~~second micromechanical structure~~ is a plated metal electrode.

6. (currently amended) The method as claimed in claim 5 further comprising preventing metal from being plated on the ~~first~~ micromechanical structure.

7. (cancel)

8. - 22. (canceled)

23. (currently amended) The method as claimed in claim 3 1 wherein the step of forming includes the step of growing the first capacitive transducer electrode via selective ~~epoxy~~ epitaxial growth.

24. (currently amended) The method as claimed in claim 3 1 wherein the step of forming includes the steps of depositing polysilicon and etching the polysilicon to form the first capacitive transducer electrode.

25. - 26. (canceled)